

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
100V	68mΩ @ V <sub>GS</sub> = 10V	4.6A
	86mΩ @ V <sub>GS</sub> = 6V	4.2A
	116mΩ @ V <sub>GS</sub> = 4.5V	3.8A

## Description

This MOSFET is designed to meet the stringent requirements of automotive applications. The device is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Power-management functions
- DC-DC converters
- Backlighting

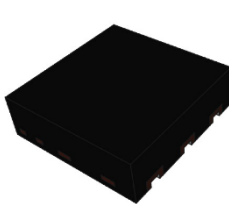
## Features

- Rated to +175°C — Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production: Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> — Ensures On-State Losses Are Minimized
- 0.6mm Profile — Ideal for Low-Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Sidewall Plated for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

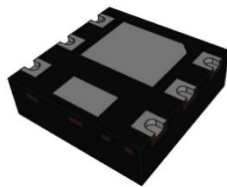
## Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.007 grams (Approximate)

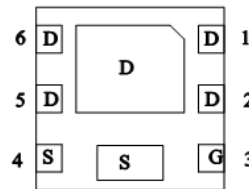
U-DFN2020-6/SWP (Type UXG)



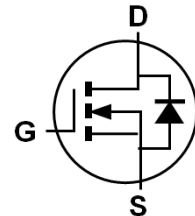
Top View



Bottom View



Pinout  
Bottom View



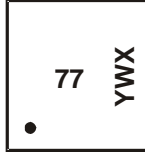
Internal Schematic

## Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMTH10H071LDFW-7	U-DFN2020-6/SWP (Type UXG)	3,000	Reel
DMTH10H071LDFW-13	U-DFN2020-6/SWP (Type UXG)	10,000	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



77 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 4 = 2024)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

### Date Code Key

Year	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035
Code	4	5	6	7	8	9	0	1	2	3	4	5

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

## Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>A</sub> = +25°C	4.6
		T <sub>A</sub> = +100°C	3.3
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	26	A
Continuous Source-Drain Diode Current (Note 6)	I <sub>S</sub>	4.6	A
Pulsed Source-Drain Diode Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	26	A
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	22	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	24.2	mJ

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	81.5	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	3	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	50	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	0.7	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu A$	$V_{DS} = 80V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	48	68	m $\Omega$	$V_{GS} = 10V, I_D = 4A$
		—	56	86		$V_{GS} = 6V, I_D = 4A$
		—	70	116		$V_{GS} = 4.5V, I_D = 2A$
Diode Forward Voltage	$V_{SD}$	—	0.8	1.0	V	$V_{GS} = 0V, I_S = 1A$
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	$C_{iss}$	—	296	—	pF	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$
Output Capacitance	$C_{oss}$	—	83	—		
Reverse Transfer Capacitance	$C_{rss}$	—	12.6	—		
Gate Resistance	$R_g$	—	11	—	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge ( $V_{GS} = 4.5V$ )	$Q_g$	—	3.4	—	nC	$V_{DS} = 50V, I_D = 4.5A$
Total Gate Charge ( $V_{GS} = 10V$ )	$Q_g$	—	6.4	—		
Gate-Source Charge	$Q_{gs}$	—	0.8	—		
Gate-Drain Charge	$Q_{gd}$	—	1.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3	—	ns	$V_{DS} = 50V, R_L = 11\Omega, V_{GS} = 10V, R_{GEN} = 3\Omega$
Turn-On Rise Time	$t_R$	—	19	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	18	—		
Turn-Off Fall Time	$t_F$	—	25	—		
Reverse-Recovery Time	$t_{RR}$	—	26	—	ns	$I_F = 4.5A, di/dt = 300A/\mu s$
Reverse-Recovery Charge	$Q_{RR}$	—	54	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

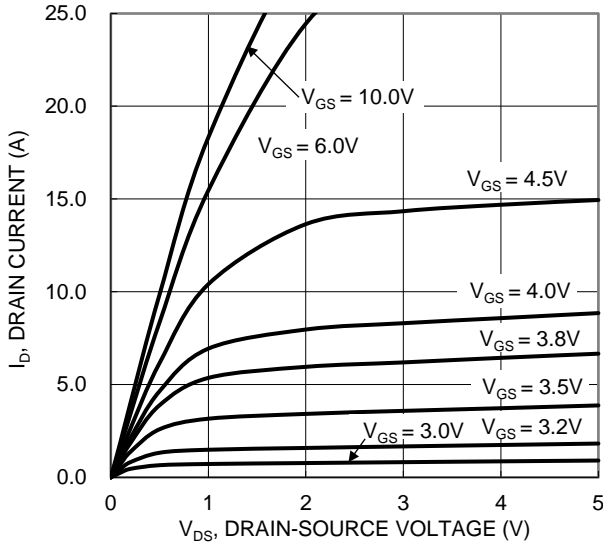


Figure 1. Typical Output Characteristic

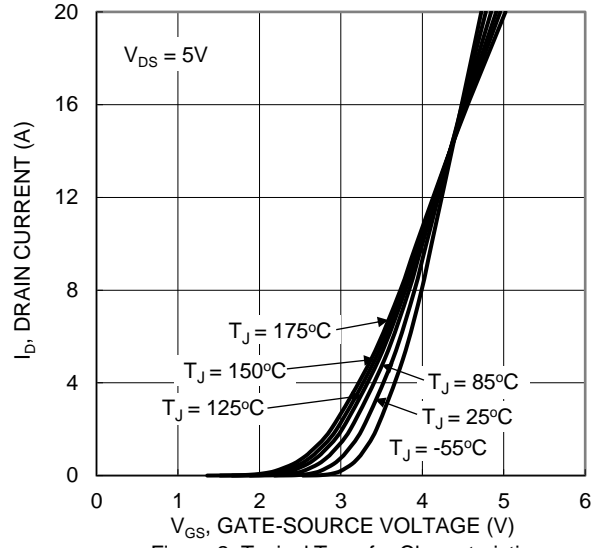


Figure 2. Typical Transfer Characteristic

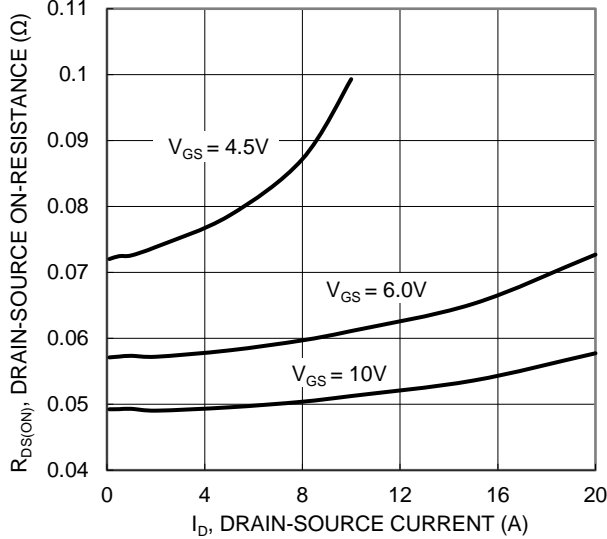


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

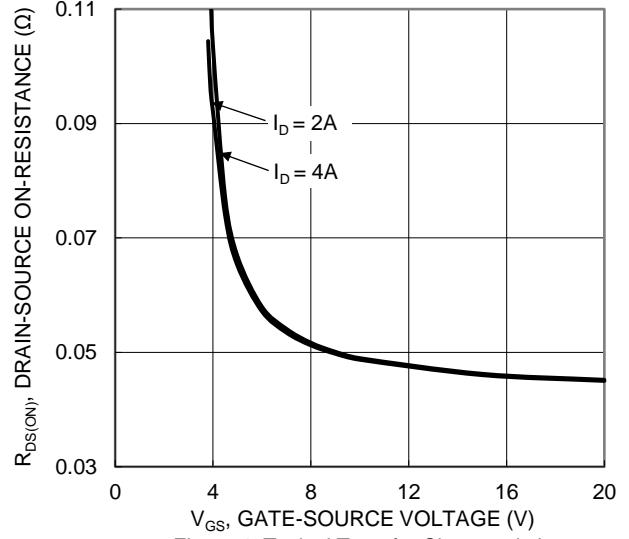


Figure 4. Typical Transfer Characteristic

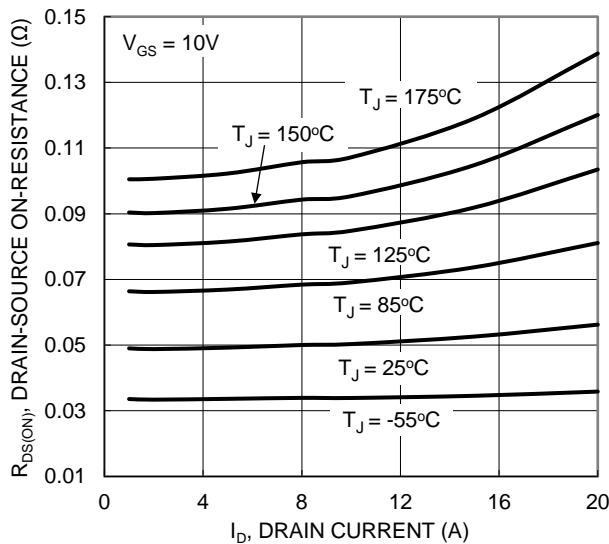


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

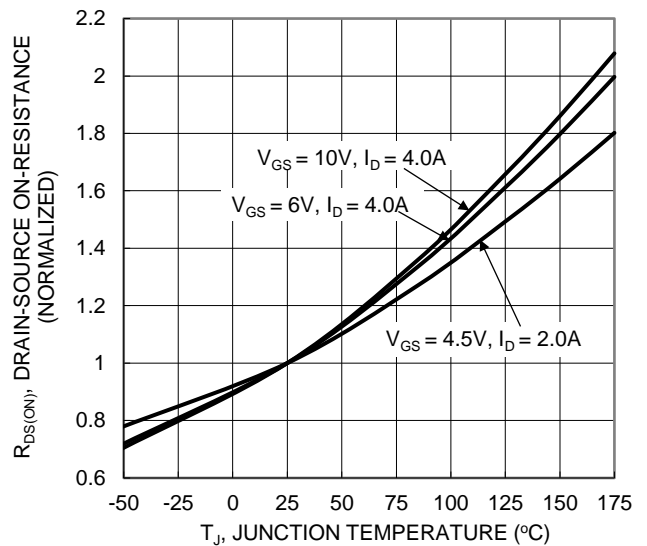


Figure 6. On-Resistance Variation with Junction Temperature

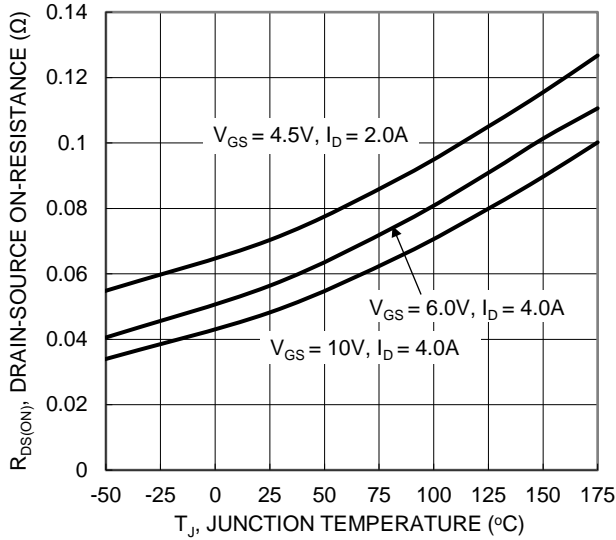


Figure 7. On-Resistance Variation with Junction Temperature

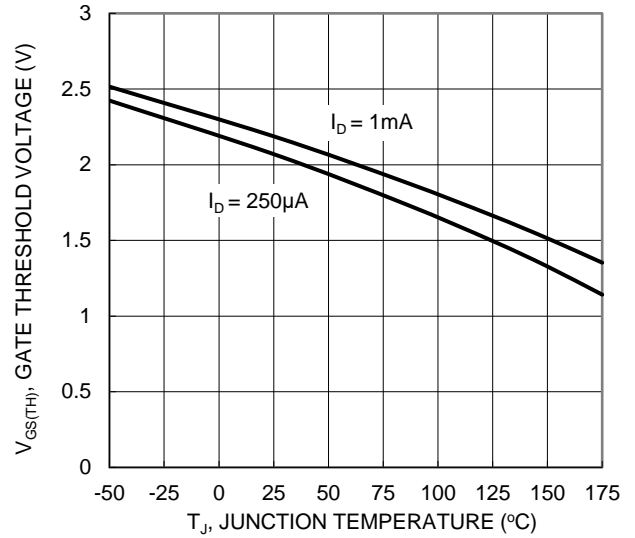


Figure 8. Gate Threshold Variation vs. Junction Temperature

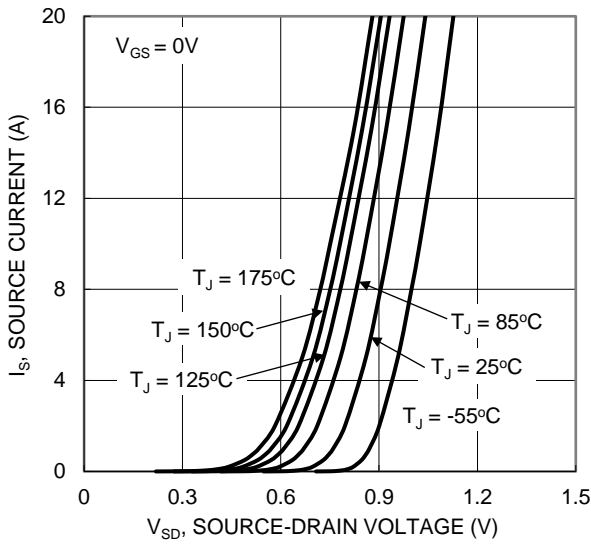


Figure 9. Diode Forward Voltage vs. Current

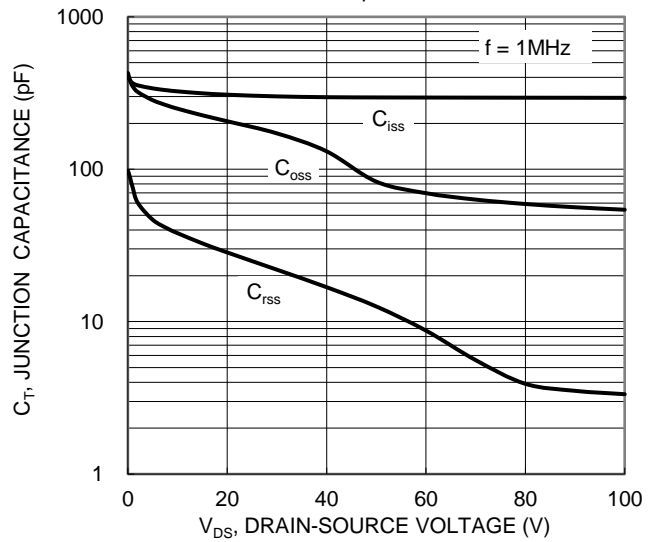


Figure 10. Typical Junction Capacitance

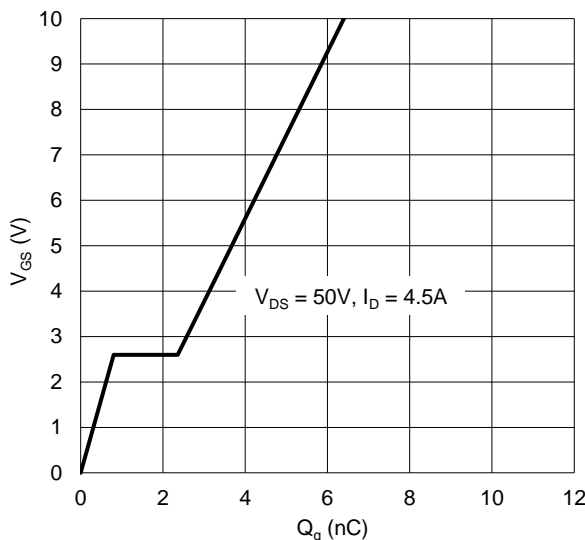


Figure 11. Gate Charge

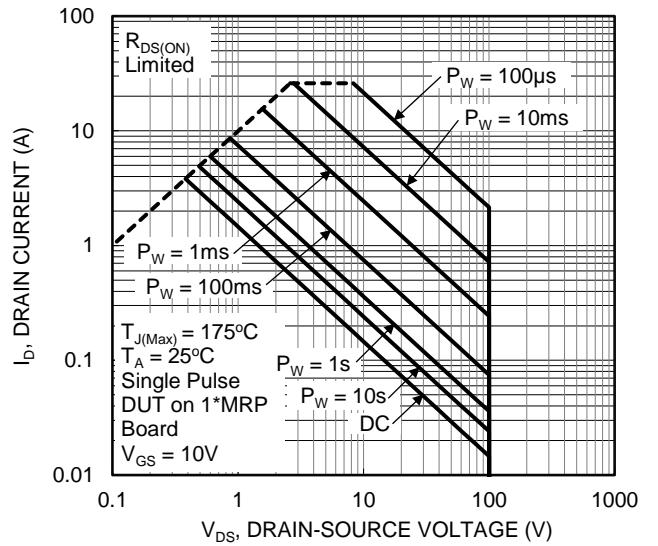


Figure 12. SOA, Safe Operation Area

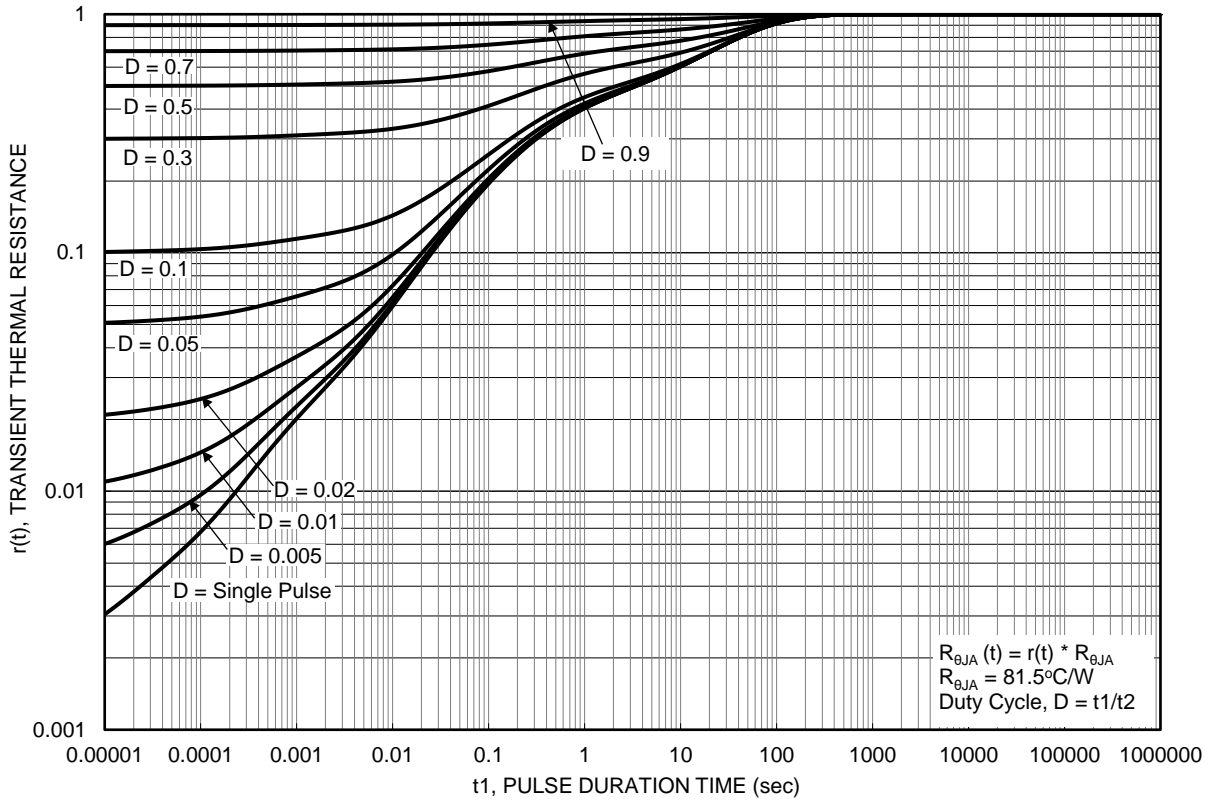


Figure 13. Transient Thermal Resistance



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